

isc N-Channel MOSFET Transistor

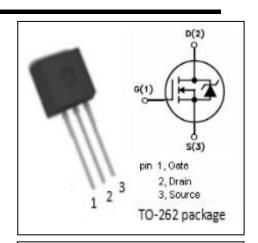
BUZ31H3046

• FEATURES

- Enhancement mode
- · Fast Switching Speed
- · 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRITION

• reliable device for use in a wide variety of applications



• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	200	V
V _G s	Gate-Source Voltage	±20	V
I _D	Drain Current-Continuous	14.5	А
I _{DM}	IDM Drain Current-Single Pulsed PD Total Dissipation @Tc=25°C Tj Max. Operating Junction Temperature Tstg Storage Temperature		A
P _D			W
Tj			${\mathbb C}$
T _{stg}			°C

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT	
Rth(ch-c)	Channel-to-case thermal resistance	1.32	°C/W	

-	T P	A.	1 5	+
D2	10	1		
Y-C-Y	Υ		ım	
	DIM	MIN	MAX	
	A	4.37	4.77	
	A1	1.22	1.42	
	A2	2.47	2.87	
	Ъ	0.70	0.97	
	Ъ2	1.17	1.42	
	С	0.28	0.53	
	D	23.20	24.02	
	D1	8.38	8.90	
	D2	6.00	-8	
	E	9.90	10.39	
	E4	7.30	_	
	е	2.5	4BSC	
	G	1.25	1.50	
	H2		1.31	
	L	13.34	14.10	
	L1	3.30	4.06	
	L3	0.95	1.15	I



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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; ID =0.25mA	200			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} ; ID =1mA	2.1		4	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =5V; I _D =9A			0.2	Ω
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±200V;V _{DS} =0V			±0.1	μ A
I _{DSS}	Drain-Source Leakage Current	V _{DS} =200V; V _{GS} = 0V			1	μА
V _{SD}	Diode forward voltage	IF=29A, V _{GS} = 0 V			1.6	V

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